

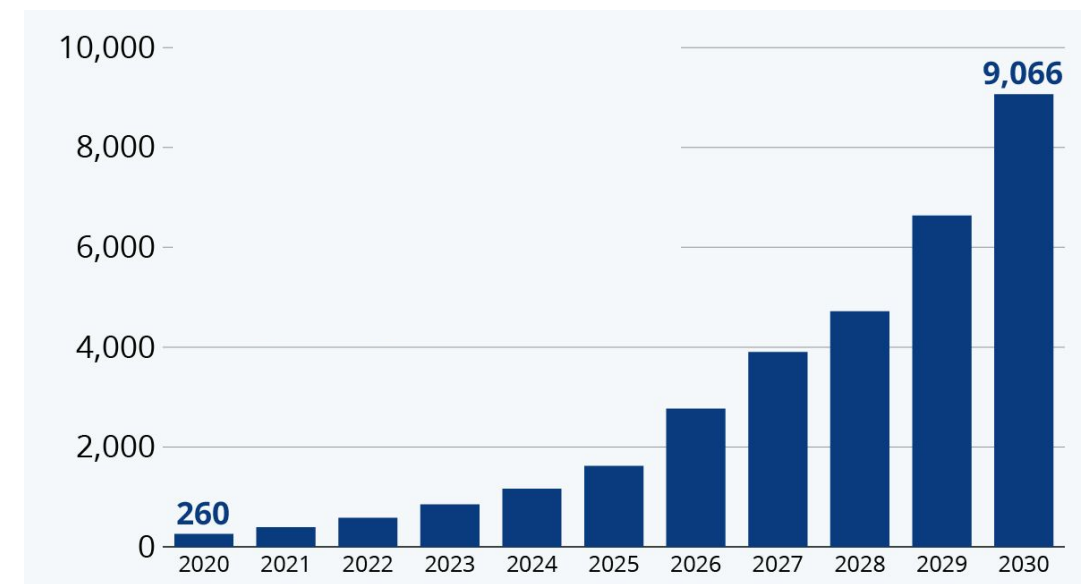
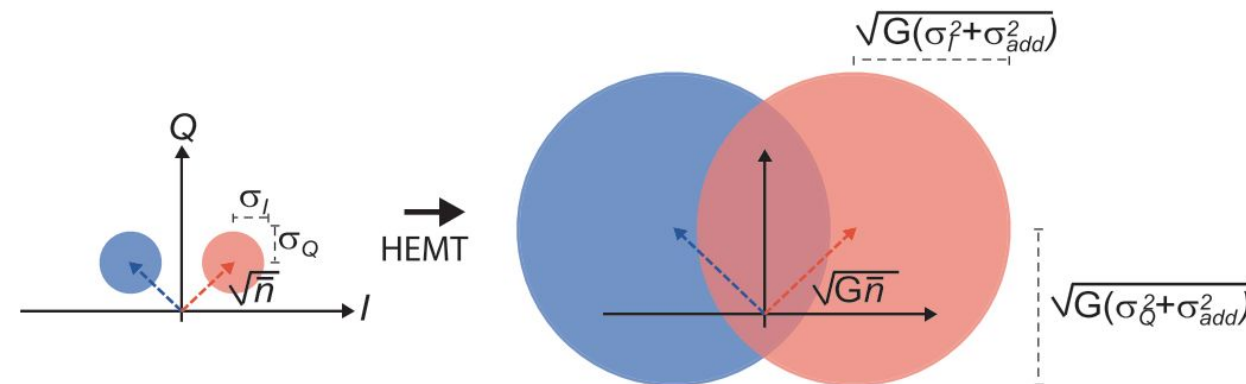
# Compact Superconducting Kinetic Inductance Traveling Wave Parametric Amplifiers with On-chip Bias Circuitry

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# Parametric Amplifier Motivation

- **Linear amplifiers always add noise**
  - Minimum added-noise given by the Quantum Limit (QL) of 0.5 quanta
- **Need high-bandwidth amplifiers operating near the QL with increased power handling**
  - Quantum tech.
  - Rare physics searches
  - Cryogenic detector readout
- **Kinetic Inductance TWPAs (KITs) a possible solution**
  - High device yield (simple fab.)
  - Elevated temperature operation (~10 K)
  - High maximum frequency (~1 THz)
  - Large dynamic range ( $P_{1dB} \sim -70$  dBm)
  - B-field-resilient (>1 T)



# Kinetic Inductance TWPAs (KITs)

- Energy conversion via modulation (pumping) of some parameter

- Three-wave mixing (3WM):  $\omega_p = \omega_s + \omega_i$
- Four-wave mixing (4WM):  $2\omega_p = \omega_s + \omega_i$

- Josephson-based amps modulate  $L_j$

- Instead use the superconducting kinetic inductance  $L_k$

$$L_k(I) \sim L_{dc} \left[ 1 + \left( \frac{I}{I_*} \right)^2 + \left( \frac{I}{I_*} \right)^4 + \dots \right]$$

$$L = L_{dc} [1 + \varepsilon I_p + \xi I_p^2 + \mathcal{O}(I^3)]$$

3WM

$$\varepsilon = \frac{2I_{dc}}{I_*^2 + I_{dc}^2}$$

4WM

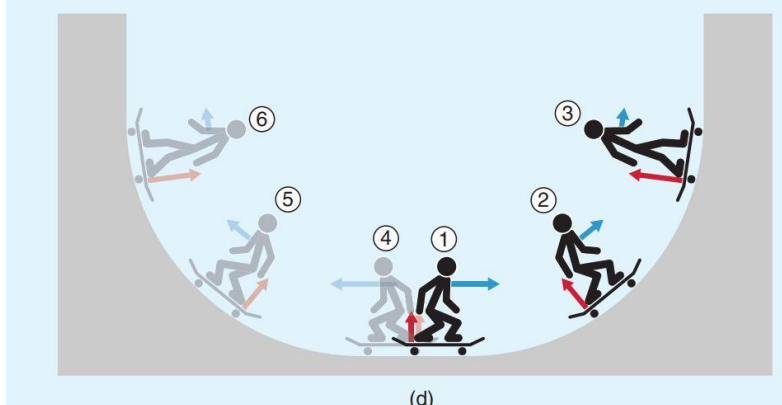
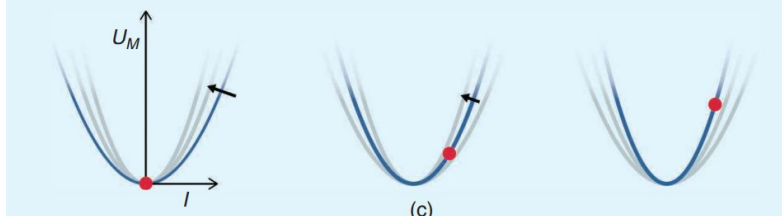
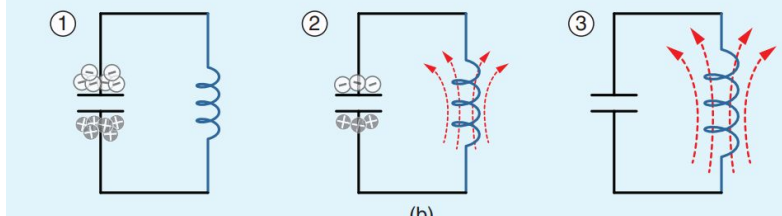
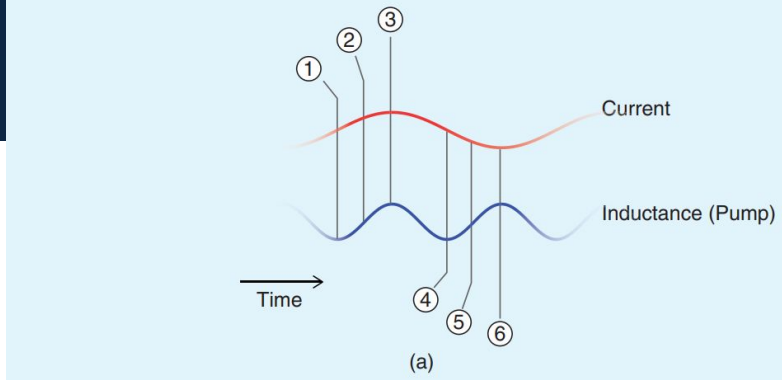
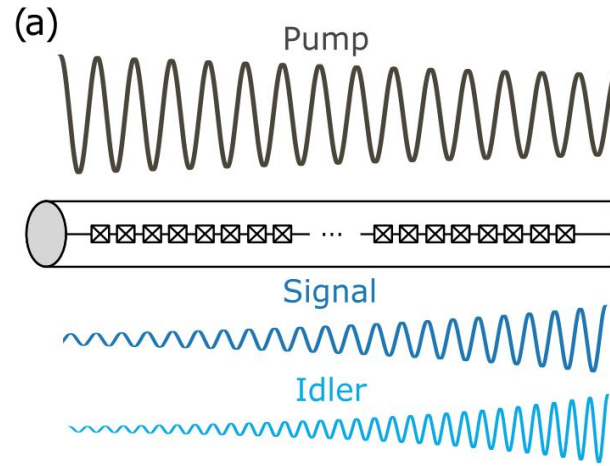
$$\xi = \frac{1}{I_*^2 + I_{dc}^2}$$

Can "turn off" 4WM with dc bias!

- Need high-kinetic-inductance materials

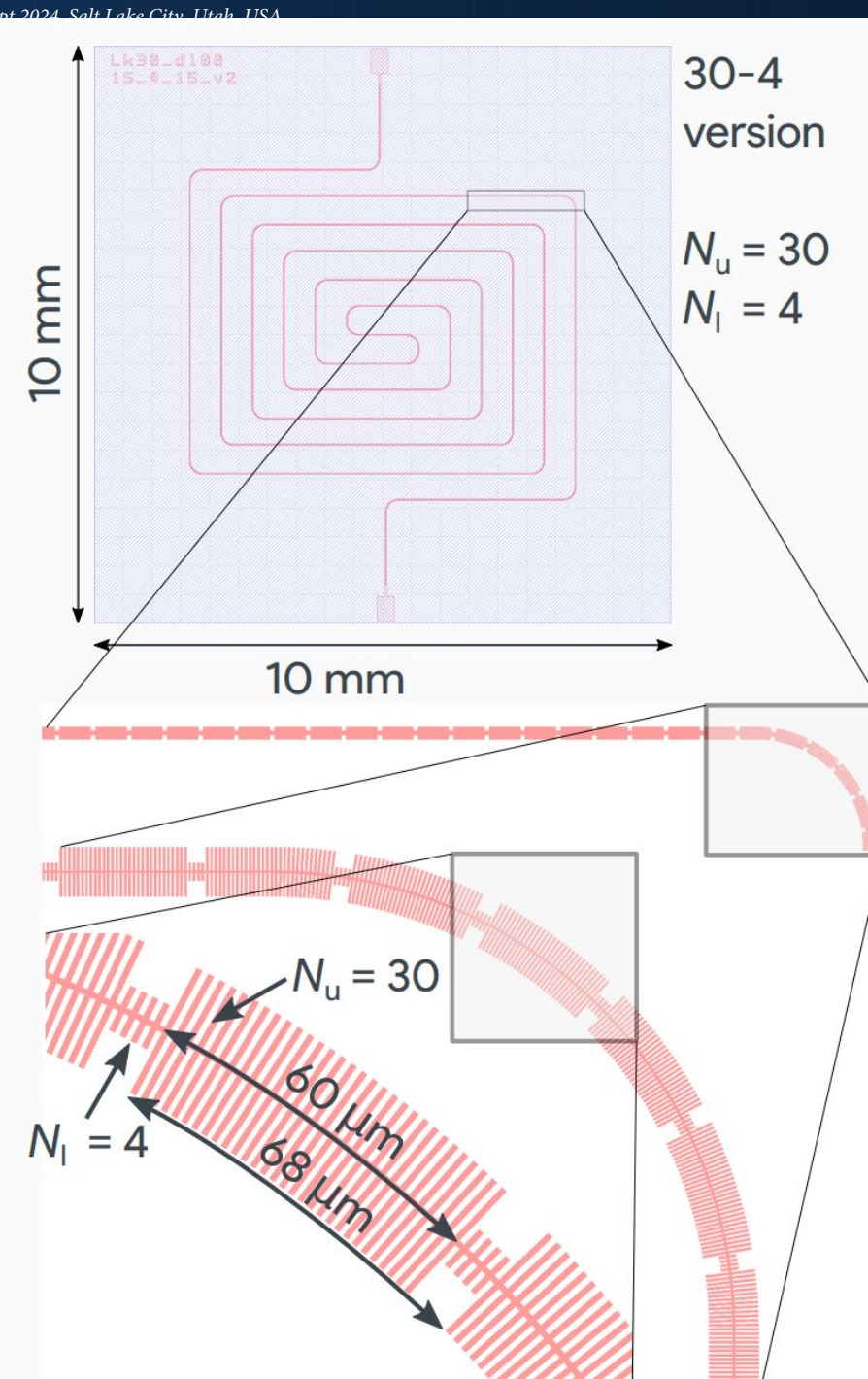
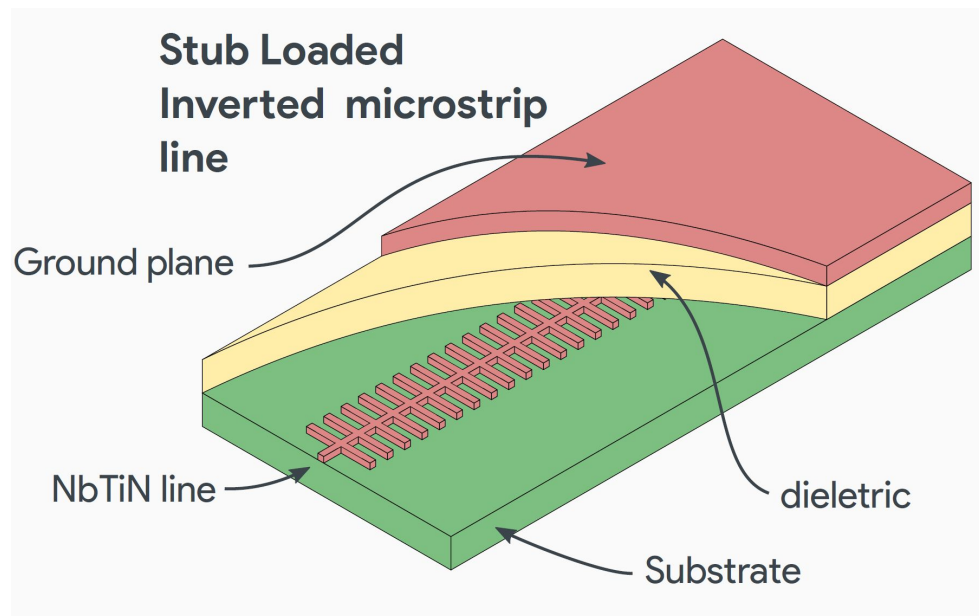
$$L_k = \frac{\hbar R_n}{\pi \Delta} \approx \frac{\hbar R_n}{1.76 \pi k_B T_c}$$

- Thin, disordered superconductors are ideal!



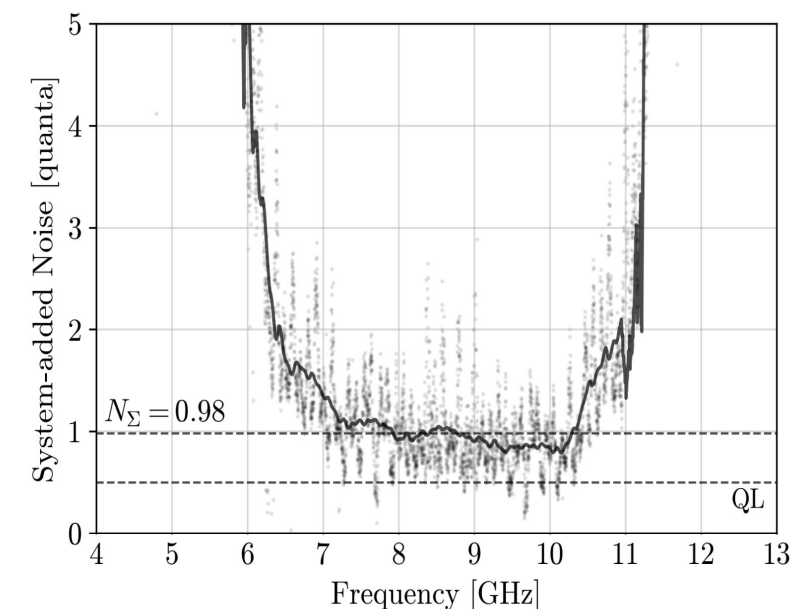
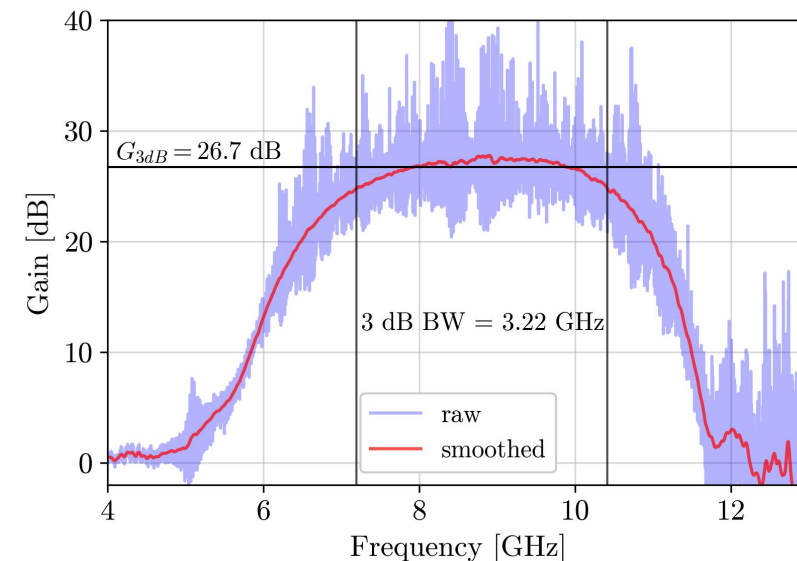
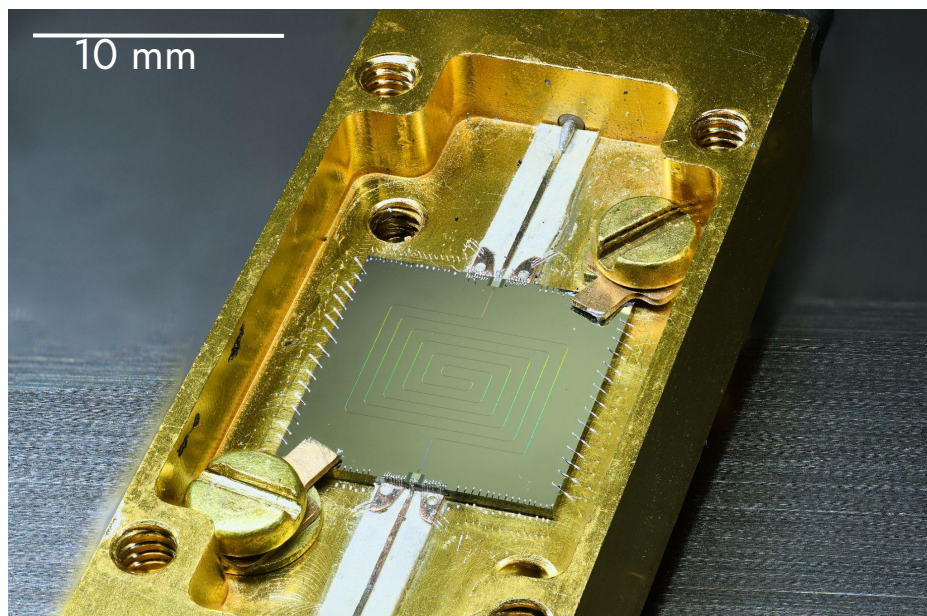
# NIST KIT Design

- Stub-loaded inverted microstrip
  - Broadband phase-matching via dispersion engineering
- ~40k unit cells  $\rightarrow$  ~8 cm length
- 10 nm NbTiN  $\rightarrow L_k = 25$  pH/sq
  - 100 nm low-loss  $\alpha$ -Si dielectric



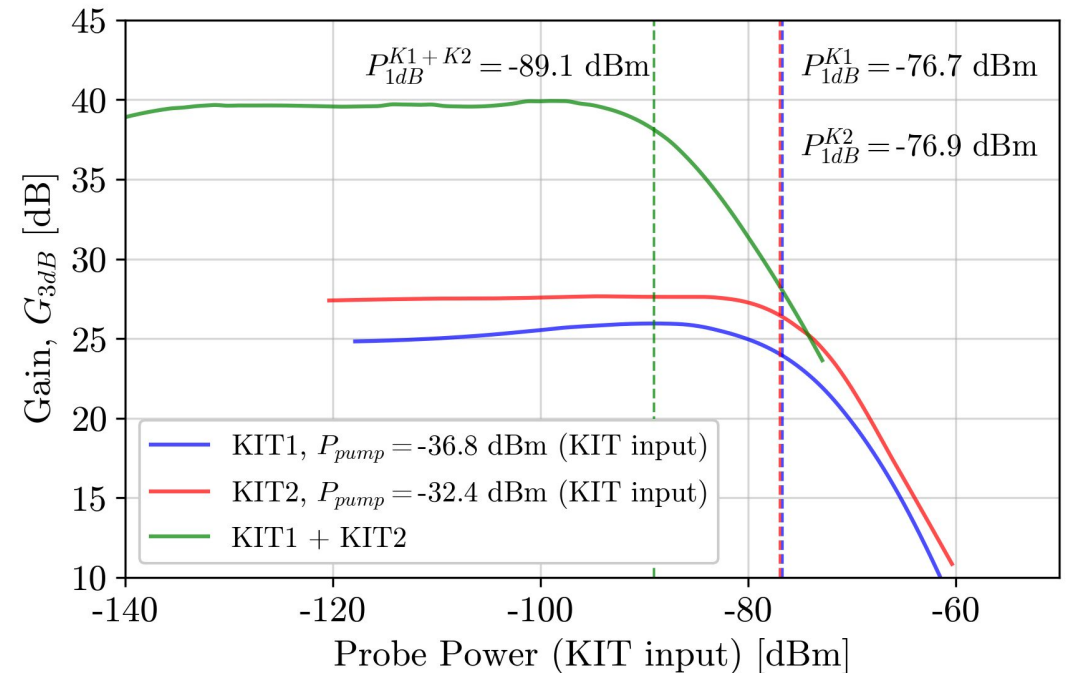
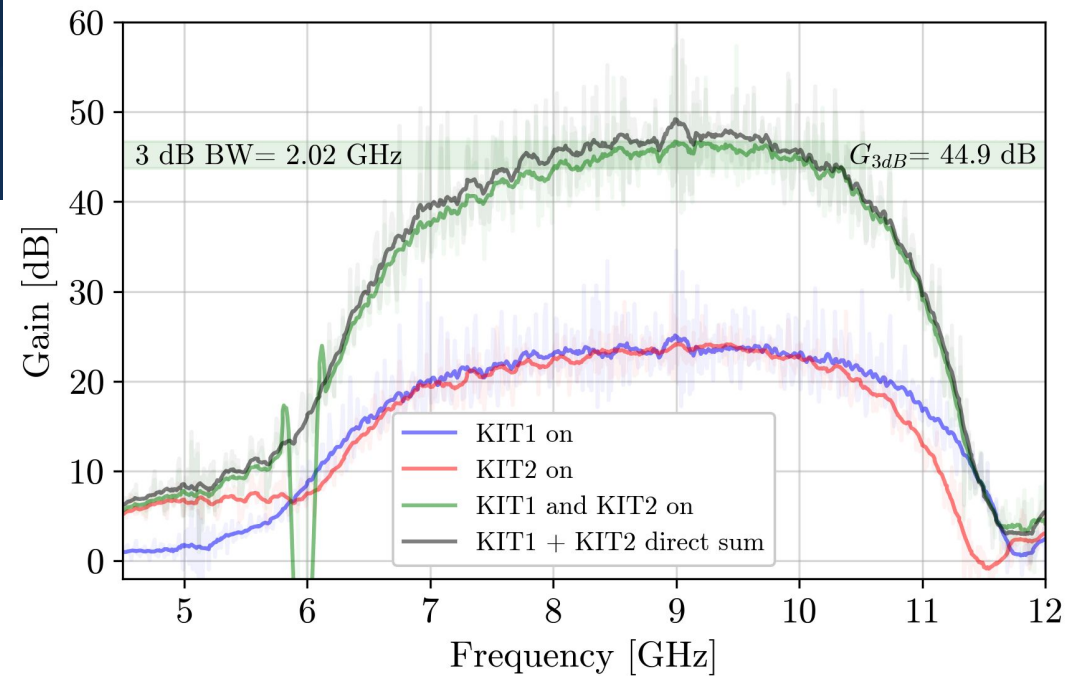
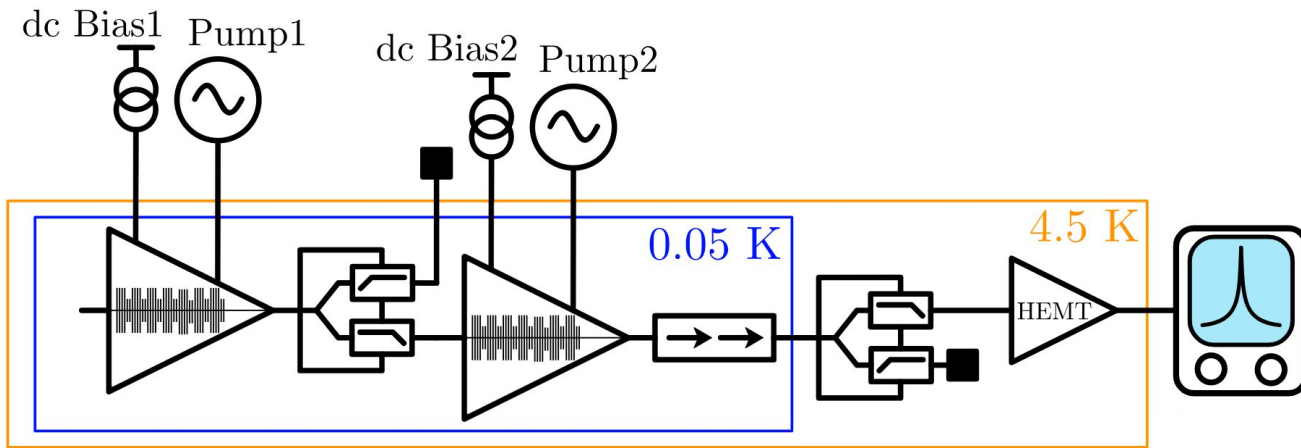
# NIST KIT v2 Performance

- Gain (on/off)  $\sim 20 - 27$  dB
- Pump power  $\sim -45$  to  $-30$  dBm (package input)
- $I_c \sim 800$   $\mu$ A
- $I_* \sim 2.8$  mA
- Bandwidth (3dB)  $\sim 3.2$  GHz
- Compression  $\sim -75$  dBm
- System noise  $\sim 1$  quanta



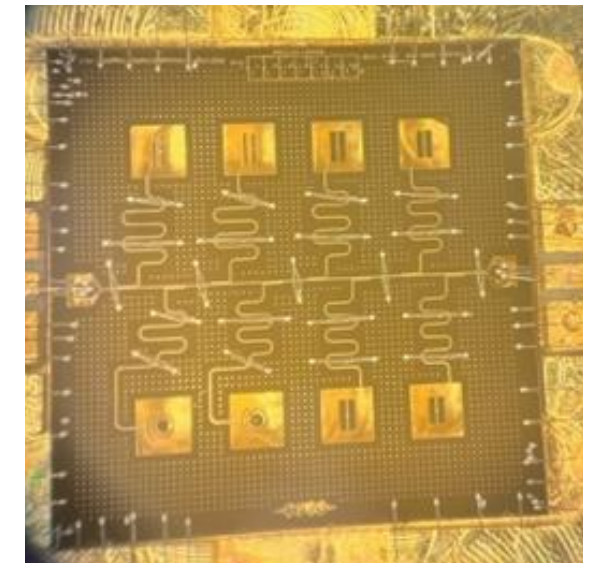
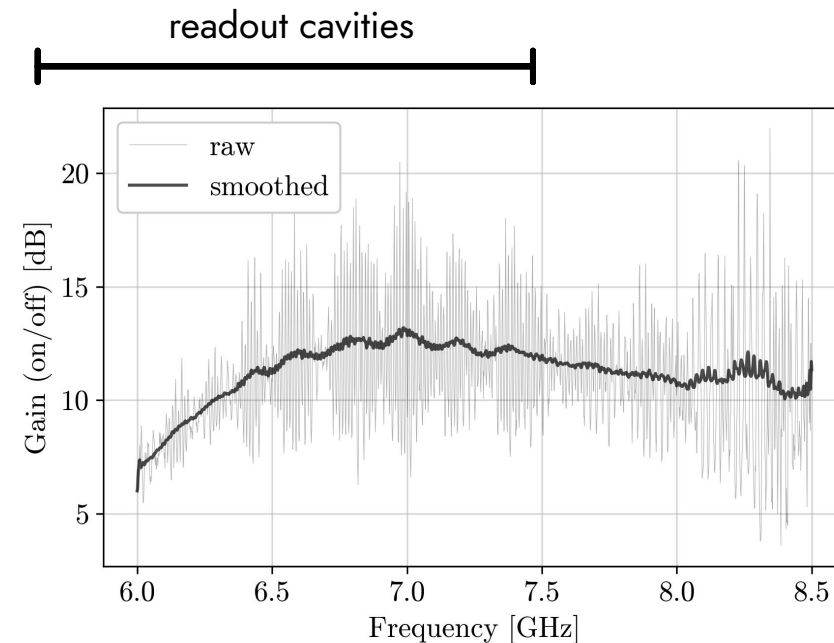
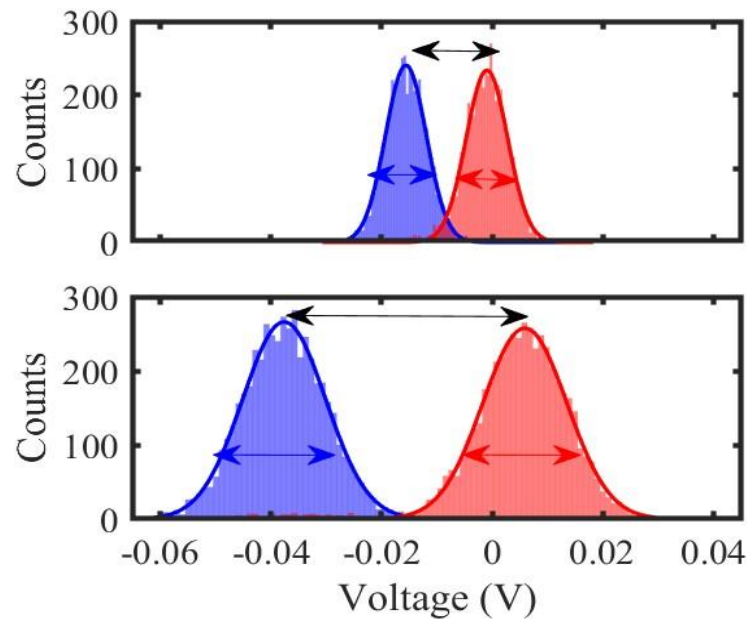
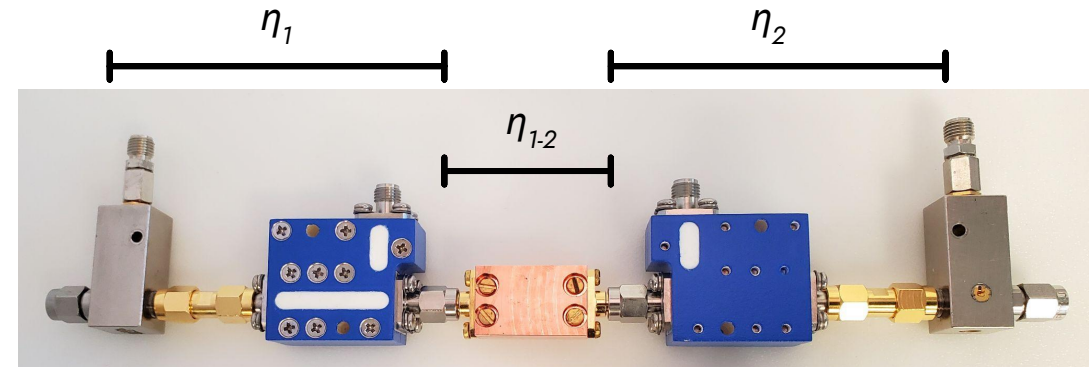
# Double KIT?

- 2 KITs in series?
  - Independent biases and pumps
- HEMT no longer necessary...? 🤔
- Possible to readout entire quantum processors with 1 KIT



# 8-qubit Readout Demo

- Goal: show a measurable improvement in readout fidelity with KIT as 1st-stage amplifier
- Results
  - Fidelity improvement from 96.2% to 97.8%
  - Signal-to-noise increase of 1.45x
  - Limited by sub-optimal KIT bandwidth / gain



# Improving KIT performance



# Impedance Mismatch and Reflections

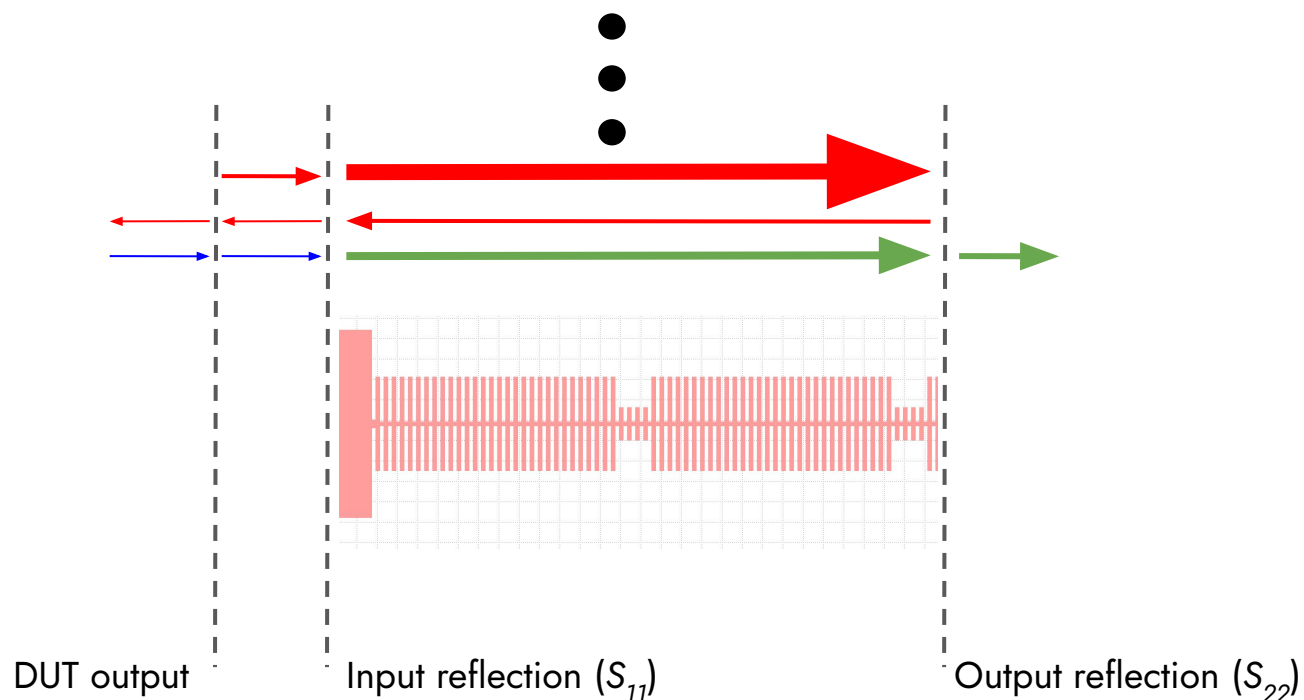
- Parametric oscillations grow exponentially
  - Pump depletion limits gain everywhere
- Consider a single mode's journey:

$$I_{out,1} = S_{21}I_{in}(1 + S_{22}S_{12}S_{11}S_{21})$$

$$S_{21} = G_K\eta_K, \quad S_{12} = \eta_K$$

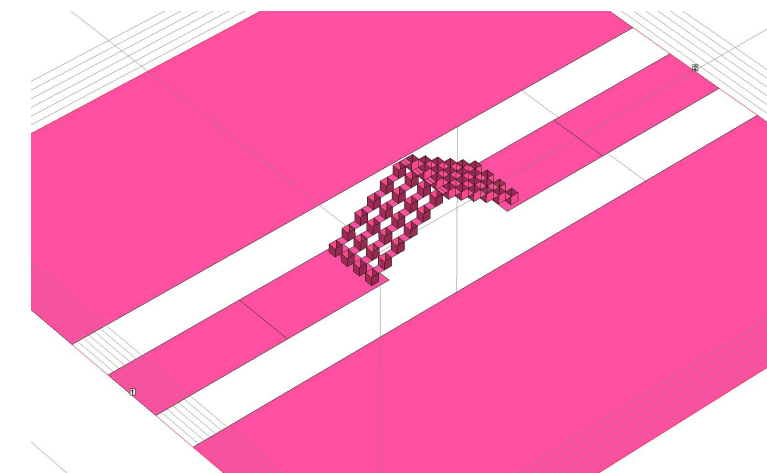
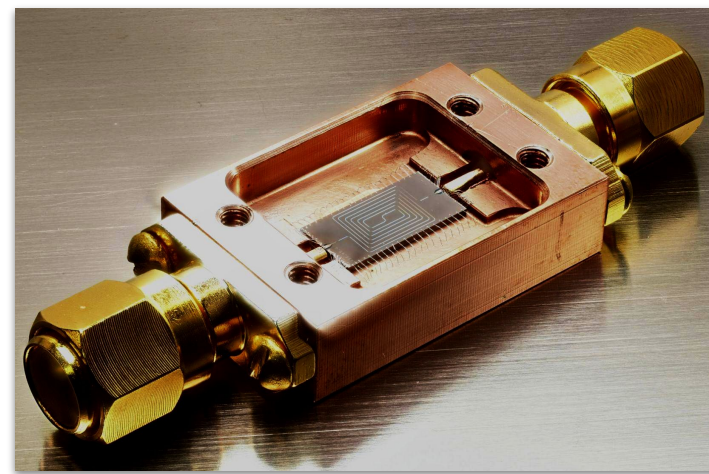
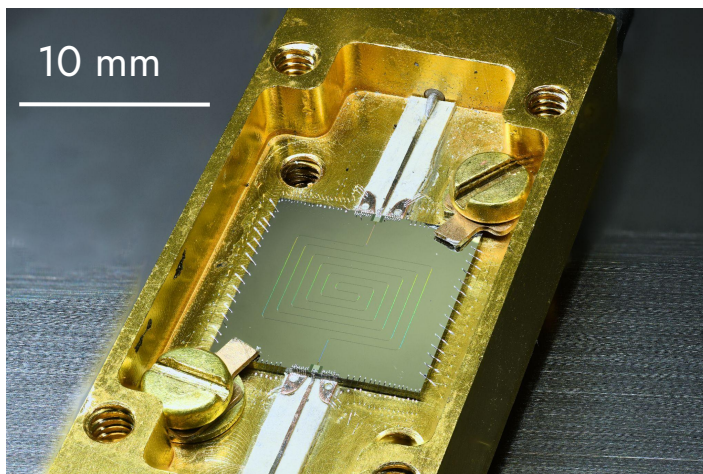
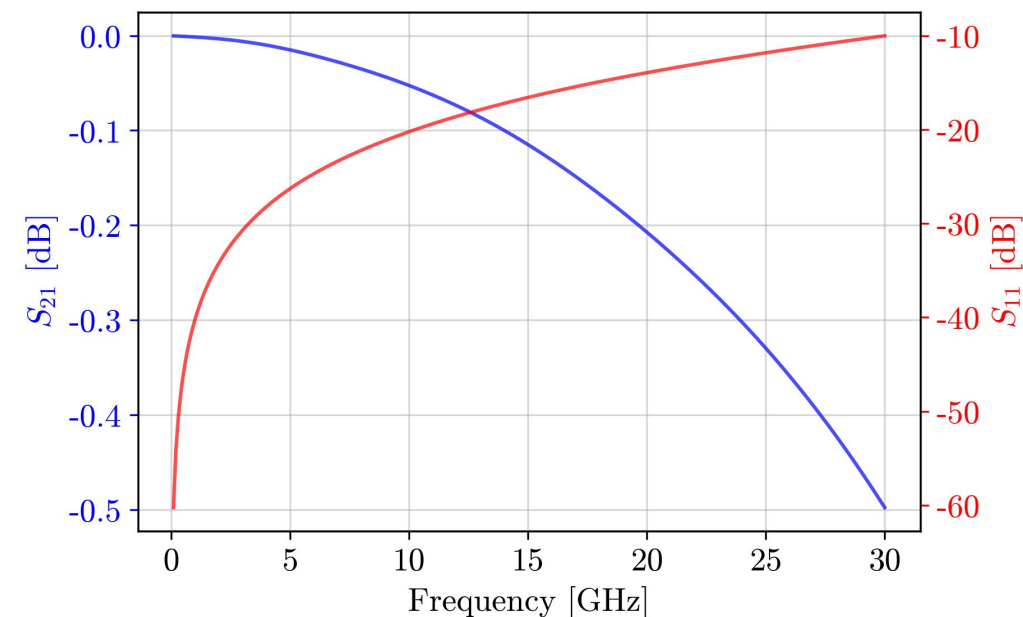
$$I_{out,n} = S_{21}I_{in} \sum_{k=0}^n (S_{22}S_{12}S_{11}S_{21})^k$$

- Sum diverges when  $G_K\eta_K^2 \geq S_{22}S_{11}$ 
  - **For 30+ dB gain (on/off) need reflections below -15 dB**
  - Smaller reflections mitigate reverse-prop. amplified noise



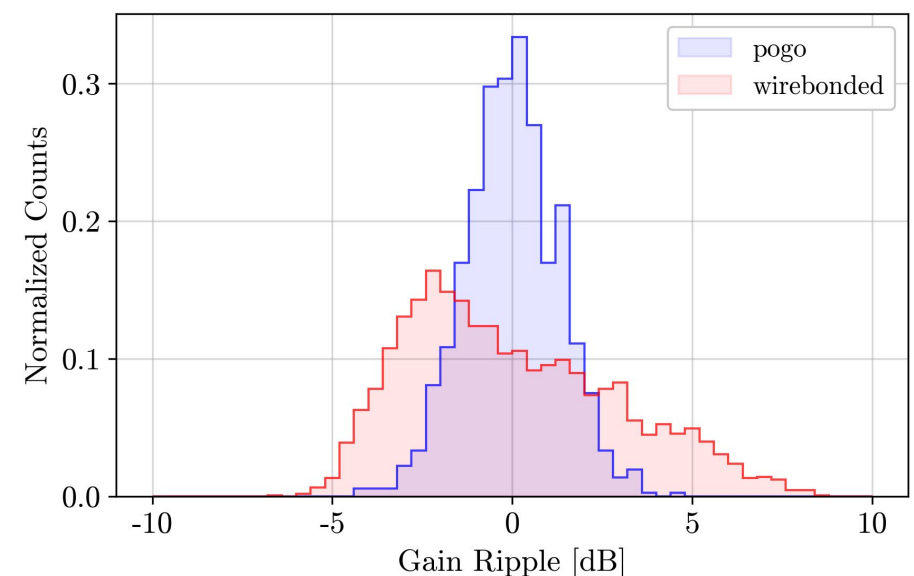
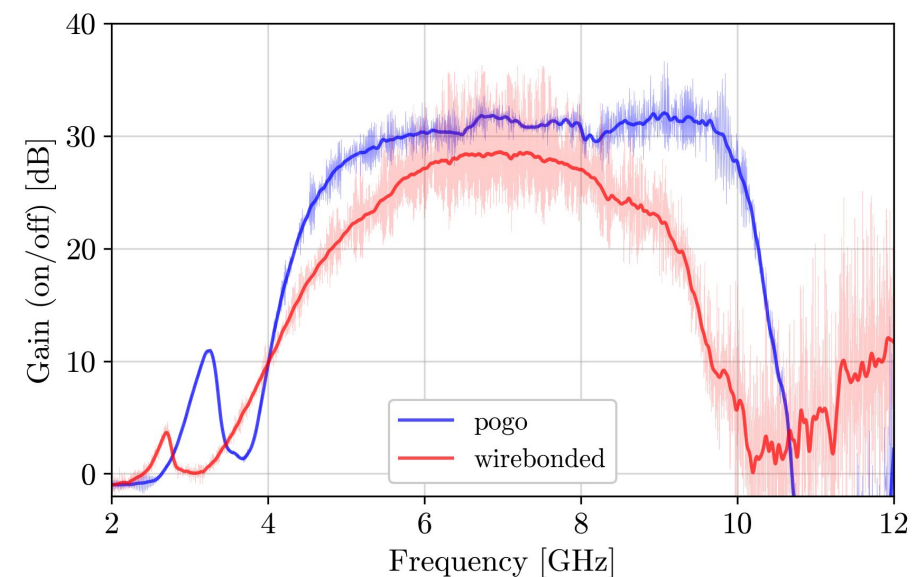
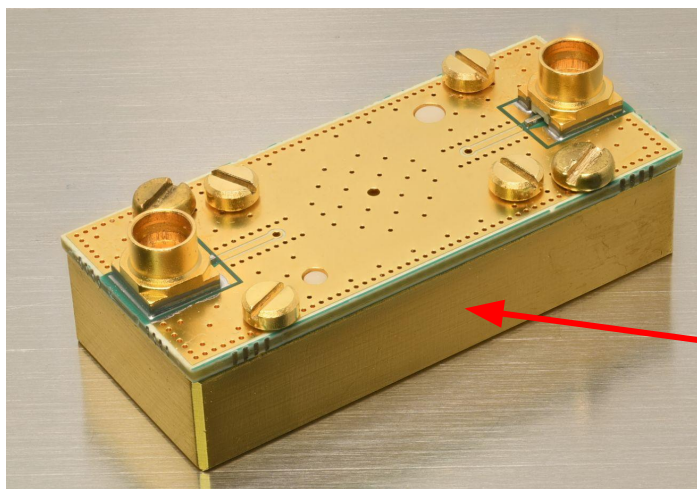
# Improving Match, Reducing Reflections

- Hitting  $Z_0 = 50 \Omega$  target
  - $Z_{0,v1} = 33 \Omega \rightarrow G \sim 13 \text{ dB}$
  - $Z_{0,v2} = 39 \Omega \rightarrow G \sim 26 \text{ dB}$
  - $Z_{0,v3} = 42 - 50 \Omega \rightarrow G > 28 \text{ dB}$
- Packaging improvements
  - Remove interface PCB (and optimize resulting launch)
  - **Stop wirebonding!**



# Eliminating Wirebonds – Pogo Pins

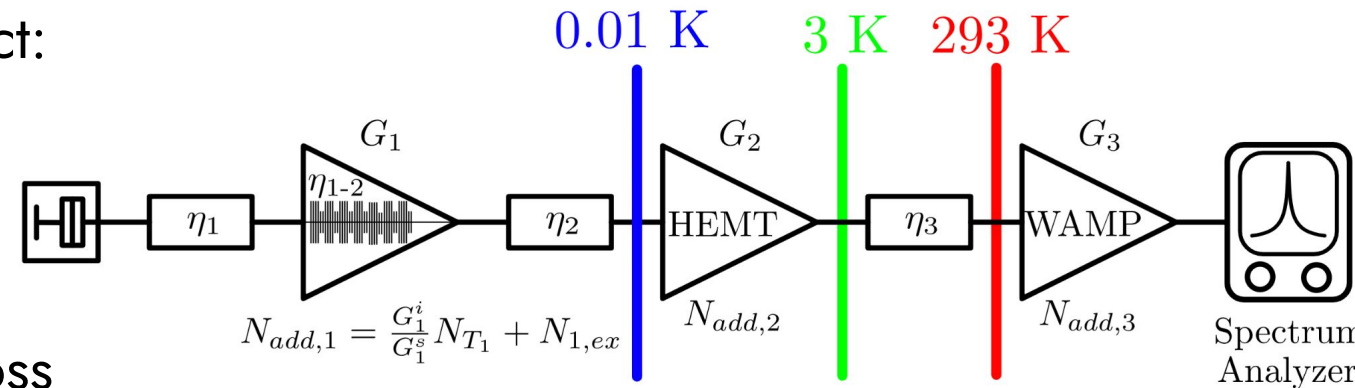
- Pogo pin benefits:
  - Drastic reduction of packaging inductance
  - Fully optimized launch:  $S_{11} < -10$  dB at 70 GHz
  - Simple, repeatable assembly: <5 min
- Results:
  - Greater max gain, lower ripple
  - Beyond-octave (4.96 GHz) bandwidth
  - Operation at higher frequencies possible (future)



# System Noise and the Impacts of Loss

- Real TWPAs are “non-ideal,” cannot neglect:

- Frequency-dependent loss
- Signal-idler gain asymmetry

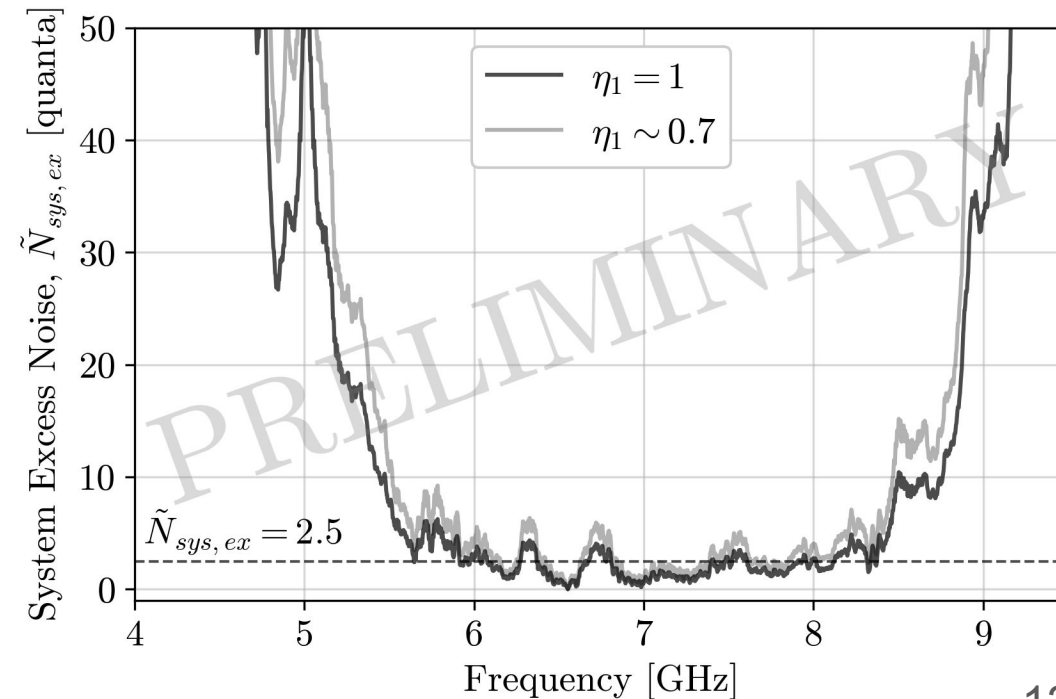


- Need to account for external component loss

$$N_{out,1}^s = \tilde{G}_1^s \left( N_{in}^s + \frac{\tilde{G}_1^i}{\tilde{G}_1^s} N_{in}^i + \tilde{N}_{1,ex}^s \right)$$

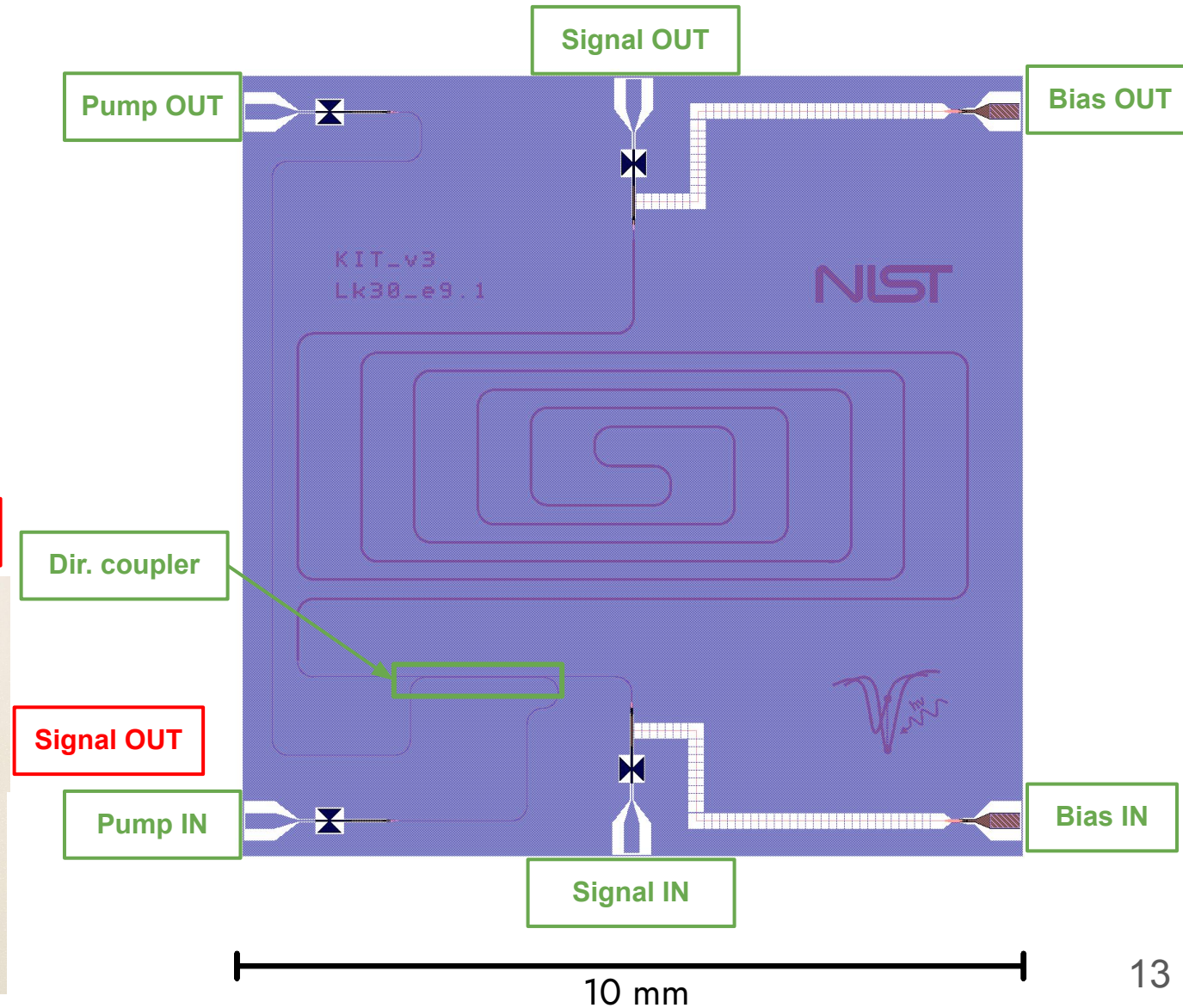
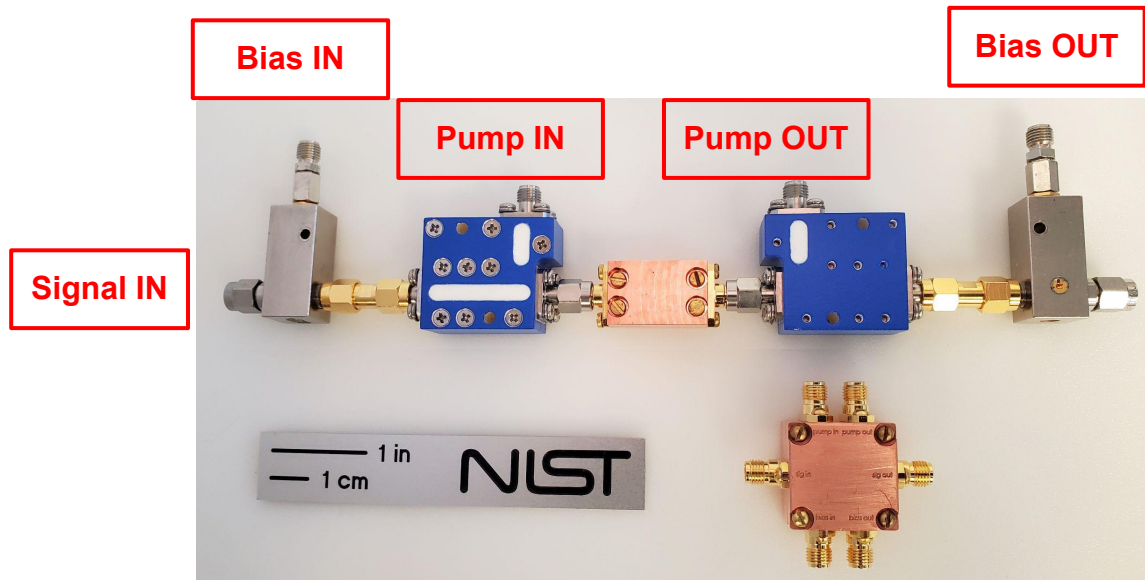
$$N_{out,3}^s = \tilde{G}_3^s \tilde{G}_2^s \tilde{G}_1^s \left( \tilde{N}_{in}^s + \frac{\tilde{G}_1^i}{\tilde{G}_1^s} N_{in}^i + \tilde{N}_{1,ex}^s \right) + \tilde{G}_3^s \tilde{G}_2^s N_{add,2}^s$$

$$\tilde{N}_{1,ex}^s = \frac{(1-\eta_1^s)N_{T1}^s + N_{1,ex}^s}{\eta_1^s} + \frac{\tilde{G}_1^i}{\tilde{G}_1^s} \frac{(1-\eta_1^i)N_{T1}^i + N_{1,ex}^i}{\eta_1^i}$$



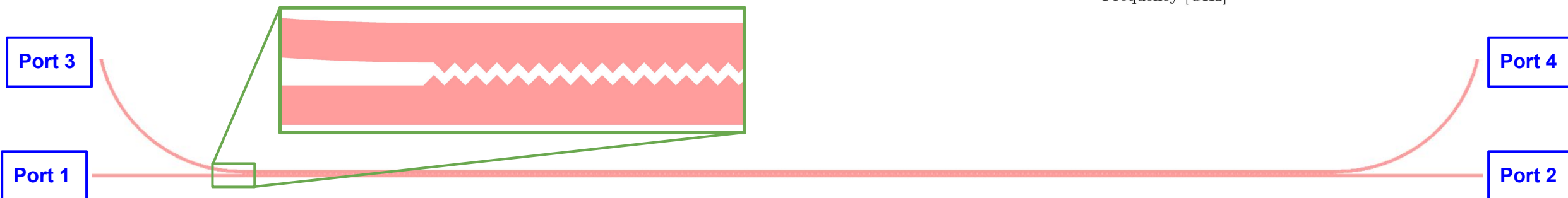
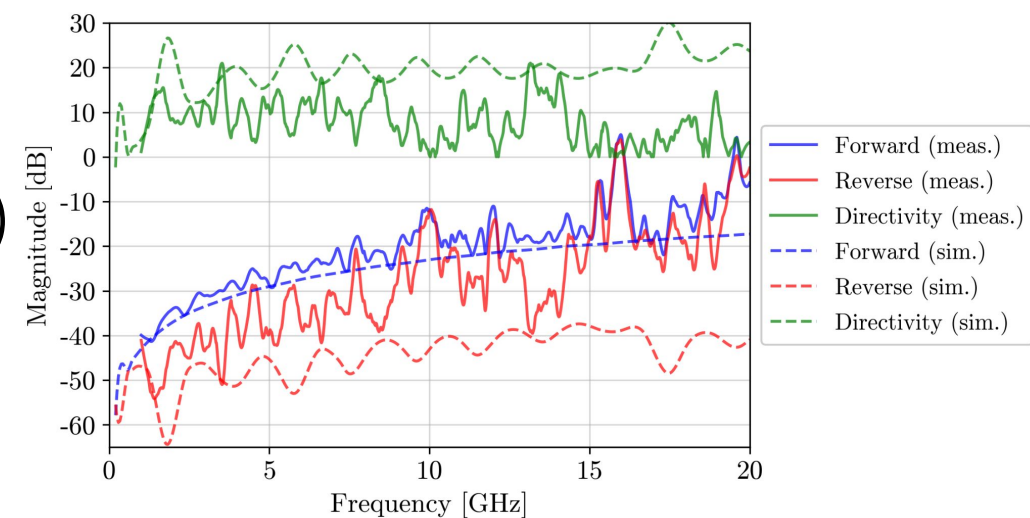
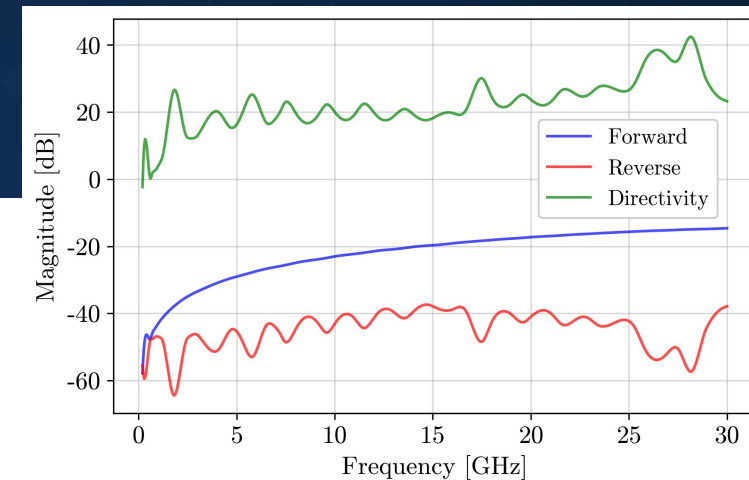
# The On-chip rf Components KIT (ORCK)

- Why put things on-chip?
  - Decrease system noise (via increasing  $\eta_1$ )
  - Compactify!
  - Reduce installation complexity
- Current approach
  - Simplicity and flexibility (broadband)
    - Bias tee
    - Directional coupler



# Directional Coupler

- Podell Wiggly Coupler (WC)
  - Ultra broadband
  - Simple geometry
  - High directivity
- Challenges
  - 100 nm dielectric + 1  $\mu\text{m}$  minimum feature size
  - Confines E-field in z direction  $\rightarrow$  long coupler (1500  $\mu\text{m}$ )
- Results (it works!)
  - Forward coupling on target
  - Directivity is lower than desired



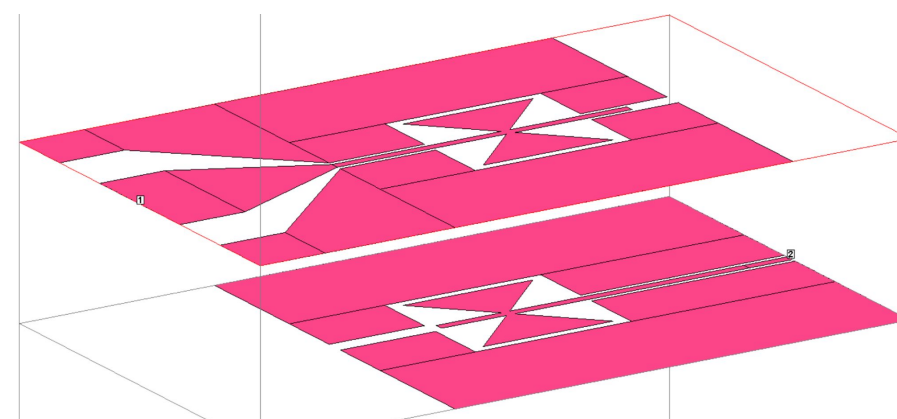
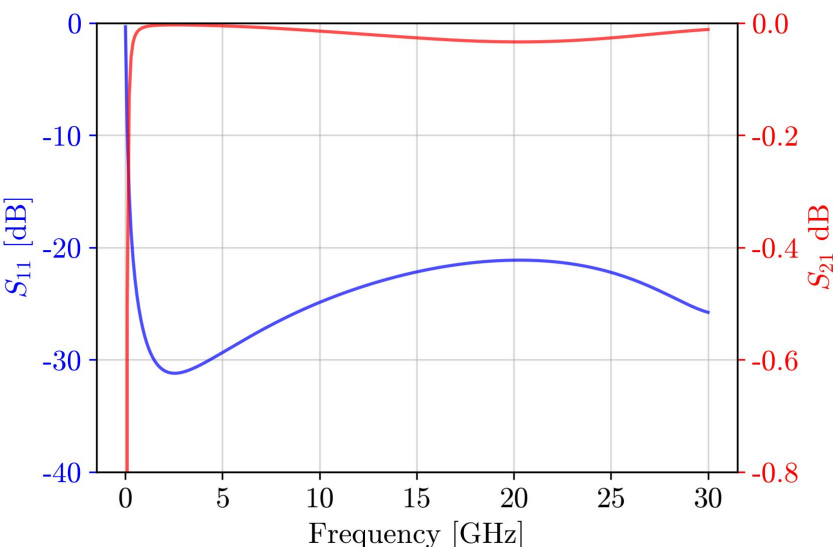
# dc Block and Microstrip Transition

- dc block developed for NIST Josephson voltage standard group

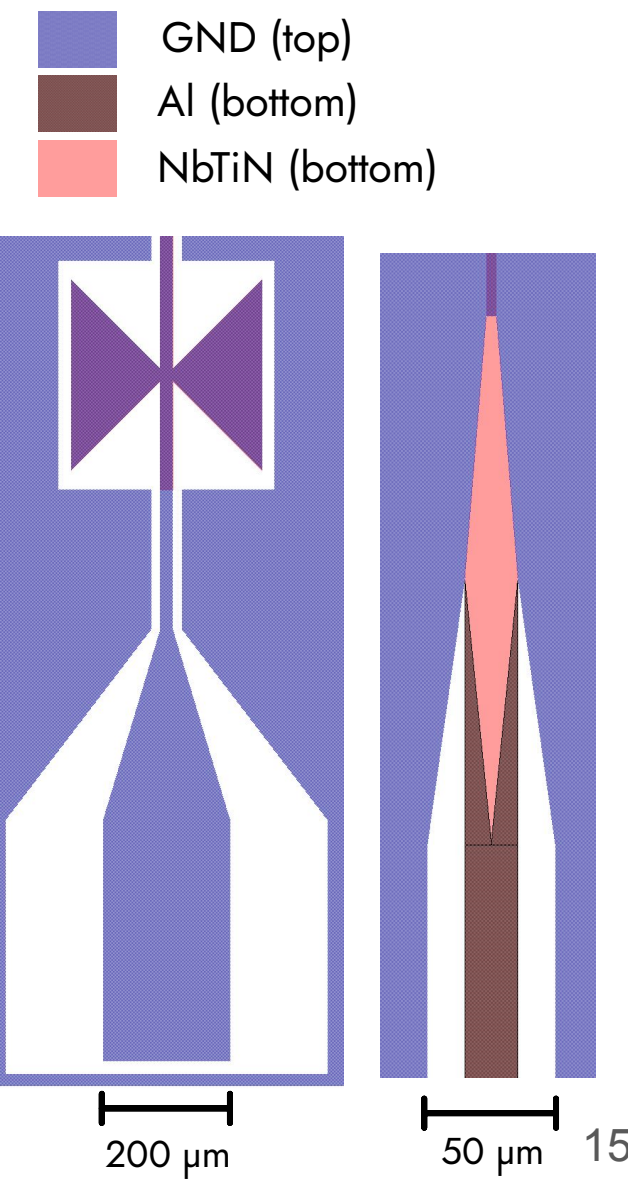
- Overlap bowtie capacitor
  - Low cutoff
  - Lumped-element at 30 GHz

- Microstrip transition:

- Less abrupt than previous design
- Gradually increases transmission line  $\mathcal{L}$ 
  - Compensates via increasing  $\mathcal{C}$

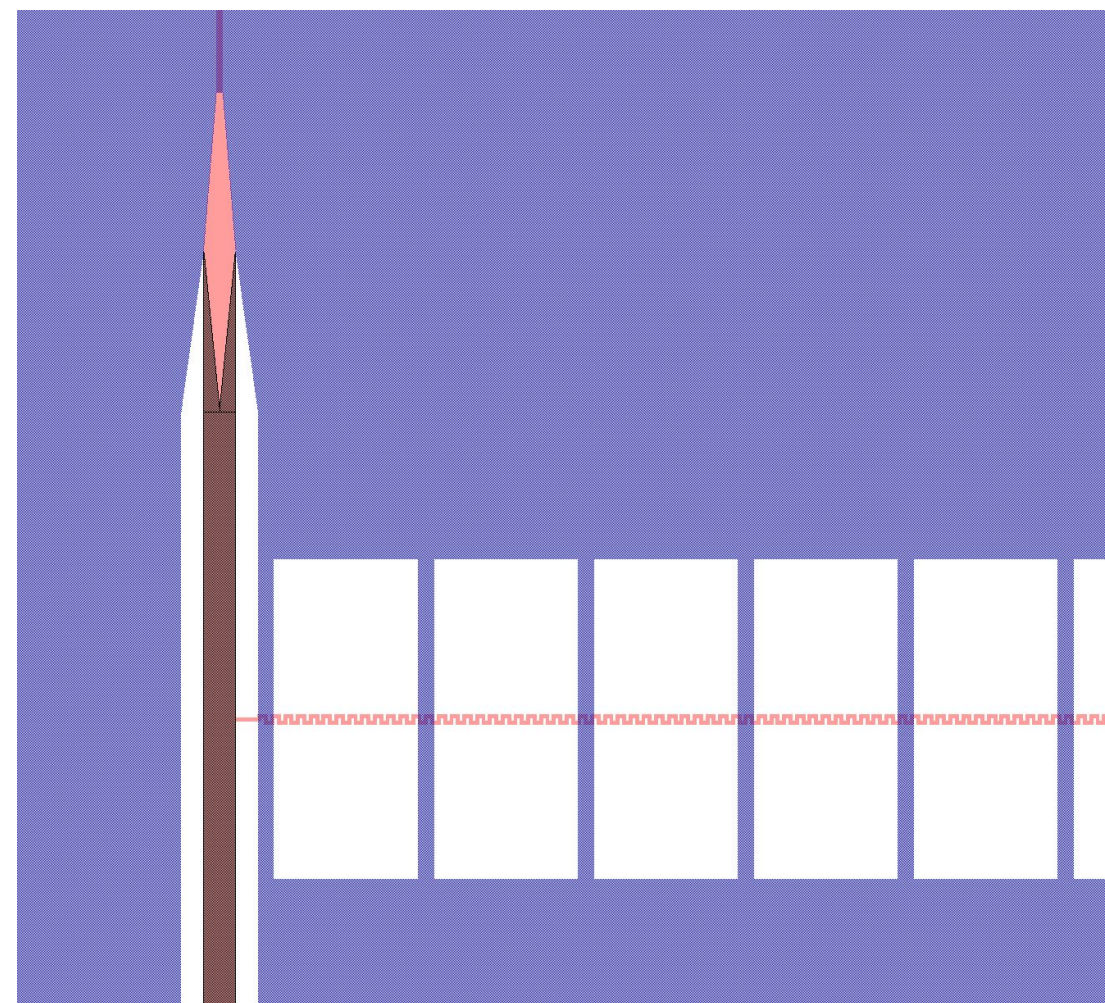
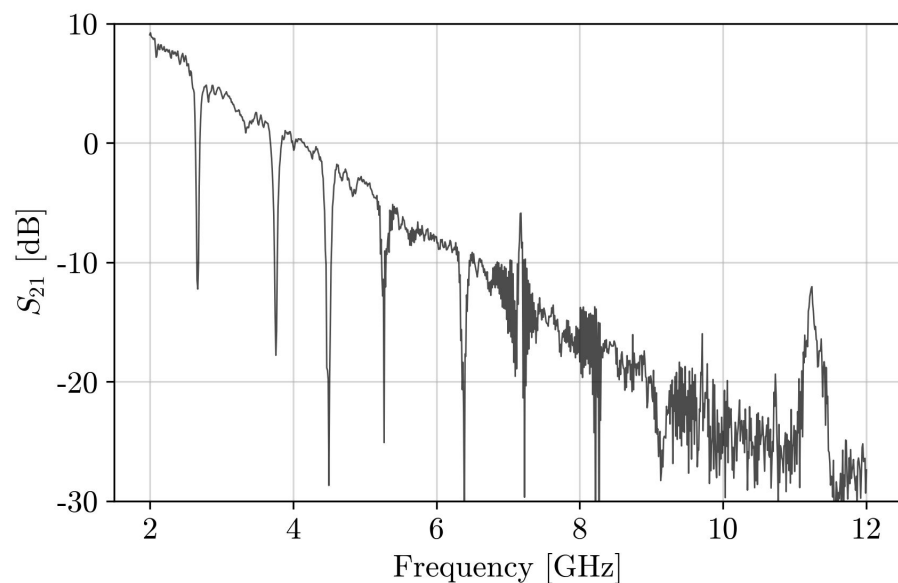


M. Elsbury - CU Boulder Thesis (2010)



# Bias Tee

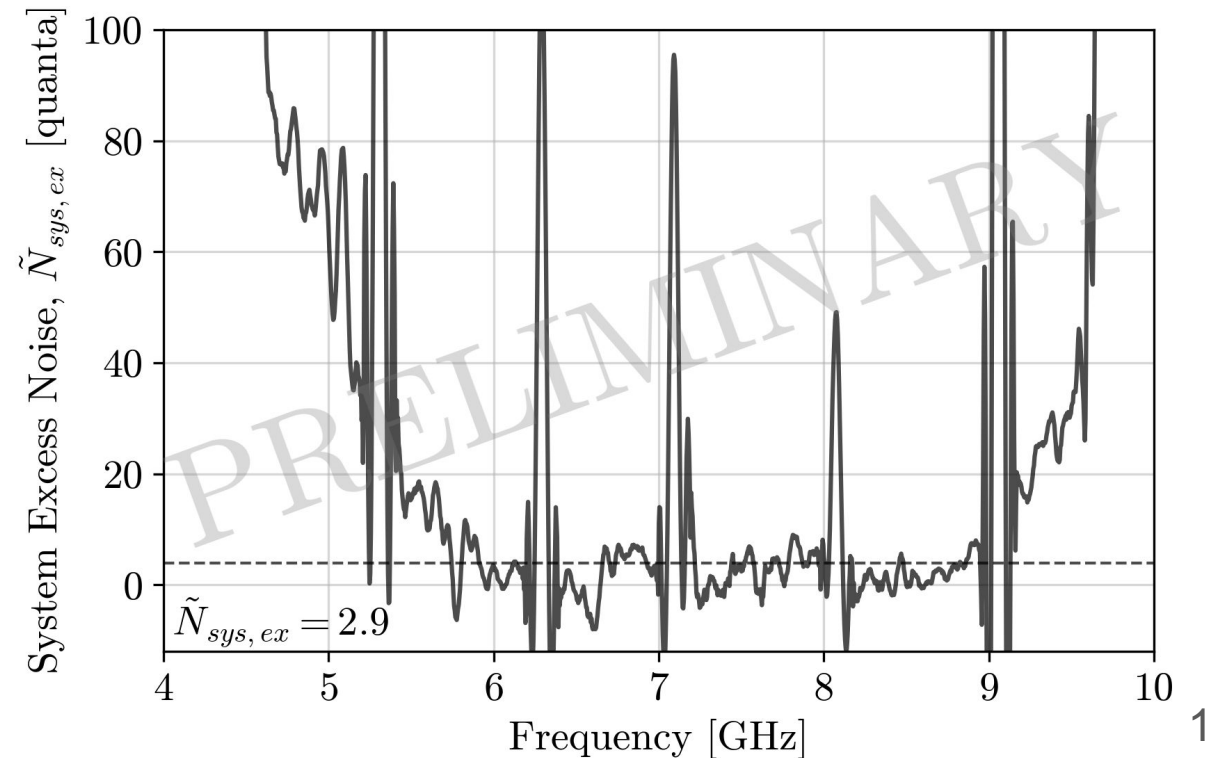
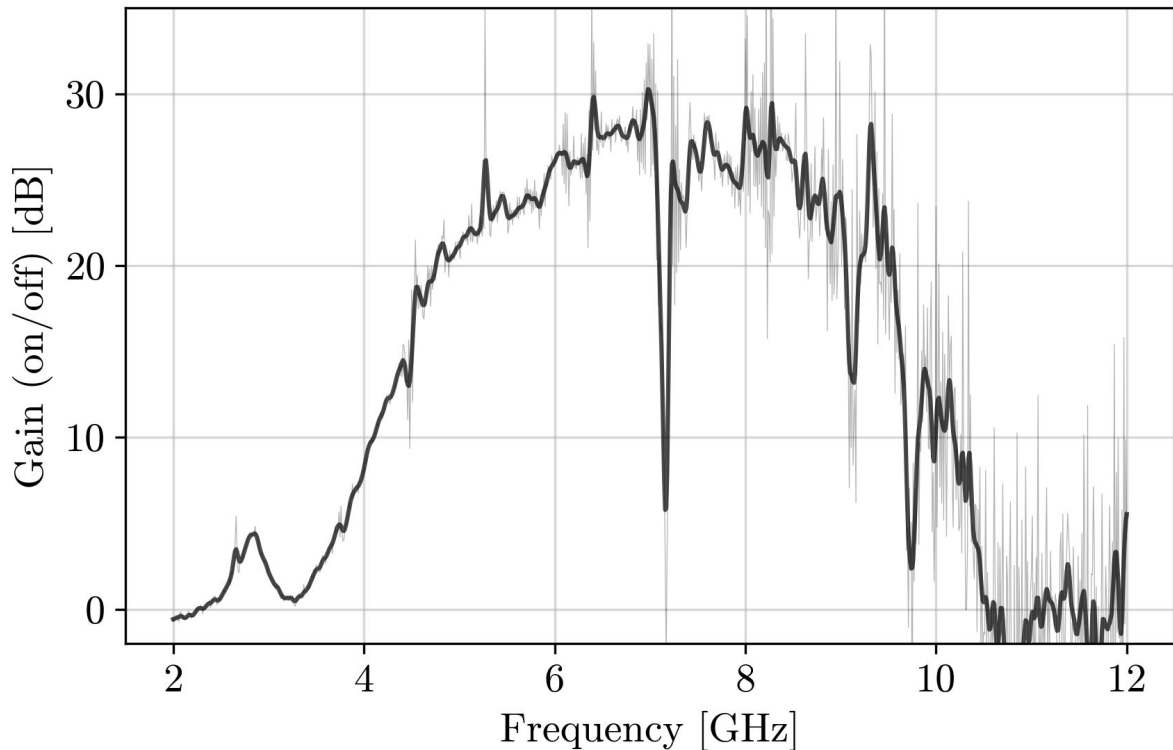
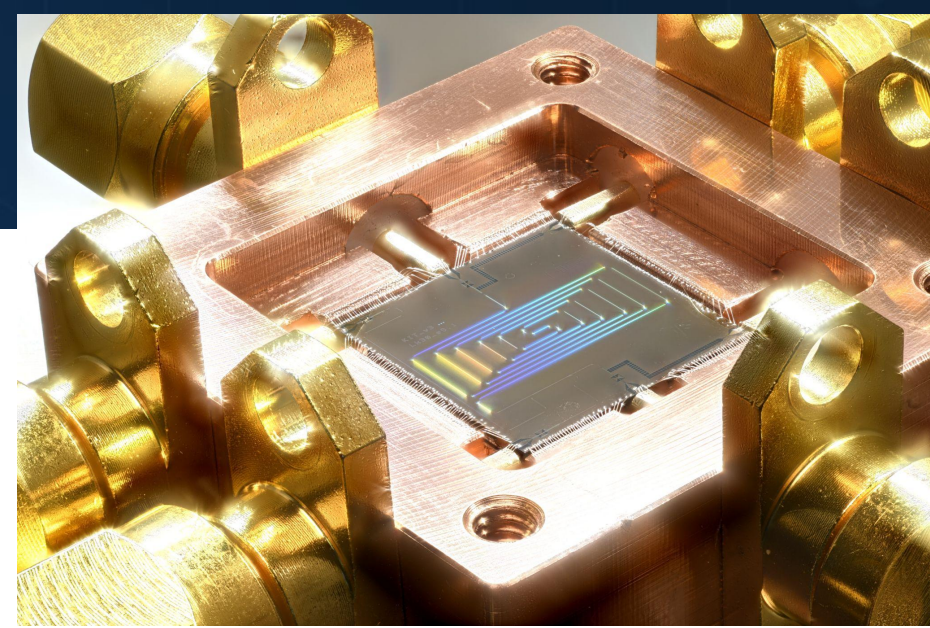
- Need  $\sim 100$  nH of inductance on dc line
  - $L_k = 25$  pH/sq for 10 nm NbTiN  $\rightarrow$  4000 sq
  - Achieve 3980 sq with meander
- Results
  - Works as a bias line!
  - $\sim 930$  MHz high-Q resonance
  - Solutions / workarounds ready for next fab run





# ORCK Performance

- $G \sim 30$  dB (on/off) still achievable
- Large usable bandwidth
  - Resonances are deep but high-Q
- System noise comparable to conventional KIT



# Conclusion

- Packaging improvements significantly enhance performance
  - $G > 30$  dB
  - Beyond-octave bandwidth
- NIST KITs are qubit-compatible
  - Demonstrated improvement in readout fidelity
- New on-chip rf bias circuits work!
  - KITs now much more compact and efficient

